

2SJ76, 2SJ77, 2SJ78, 2SJ79

Silicon P-Channel MOS FET

HITACHI

November 1996

Application

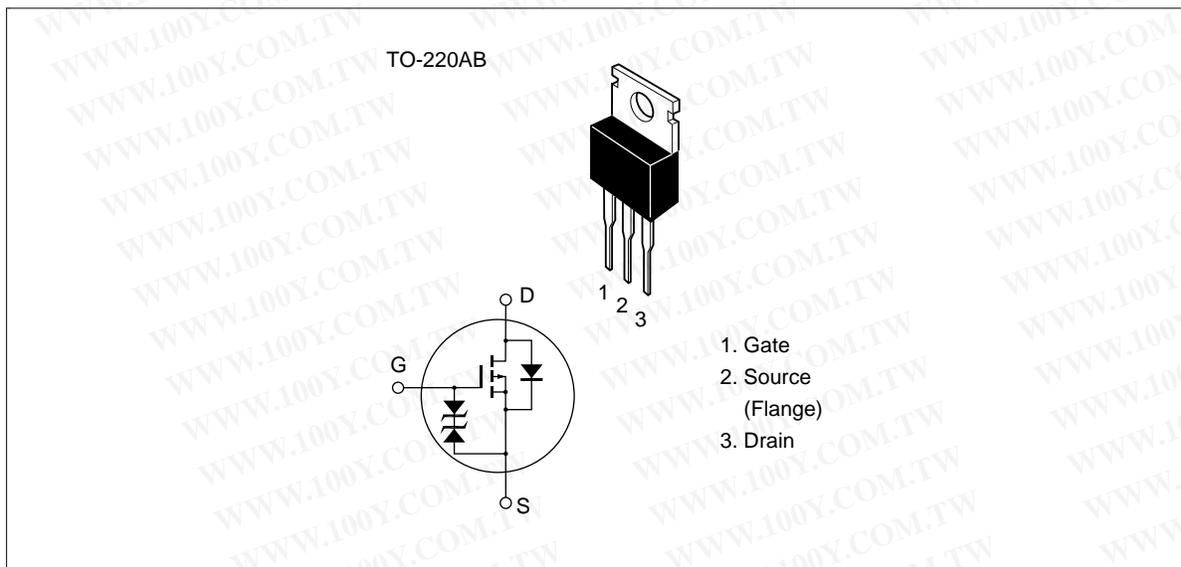
High frequency and low frequency power amplifier, high speed power switching

Complementary pair with 2SK213, 2SK214, 2SK215, 2SK216

Features

- Suitable for direct mounting
- High forward transfer admittance
- Excellent frequency response
- Enhancement-mode

Outline



勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-34970699
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

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Absolute Maximum Ratings (Ta = 25°C)

| Item | | Symbol | Ratings | Unit |
|---|-------|-----------|-------------|------|
| Drain to source voltage | 2SJ76 | V_{DSX} | -140 | V |
| | 2SJ77 | | -160 | |
| | 2SJ78 | | -180 | |
| | 2SJ79 | | -200 | |
| Gate to source voltage | | V_{GSS} | ±15 | V |
| Drain current | | I_D | -500 | mA |
| Body to drain diode reverse drain current | | I_{DR} | -500 | mA |
| Channel dissipation | | Pch | 1.75 | W |
| | | Pch*1 | 30 | W |
| Channel temperature | | Tch | 150 | °C |
| Storage temperature | | Tstg | -45 to +150 | °C |

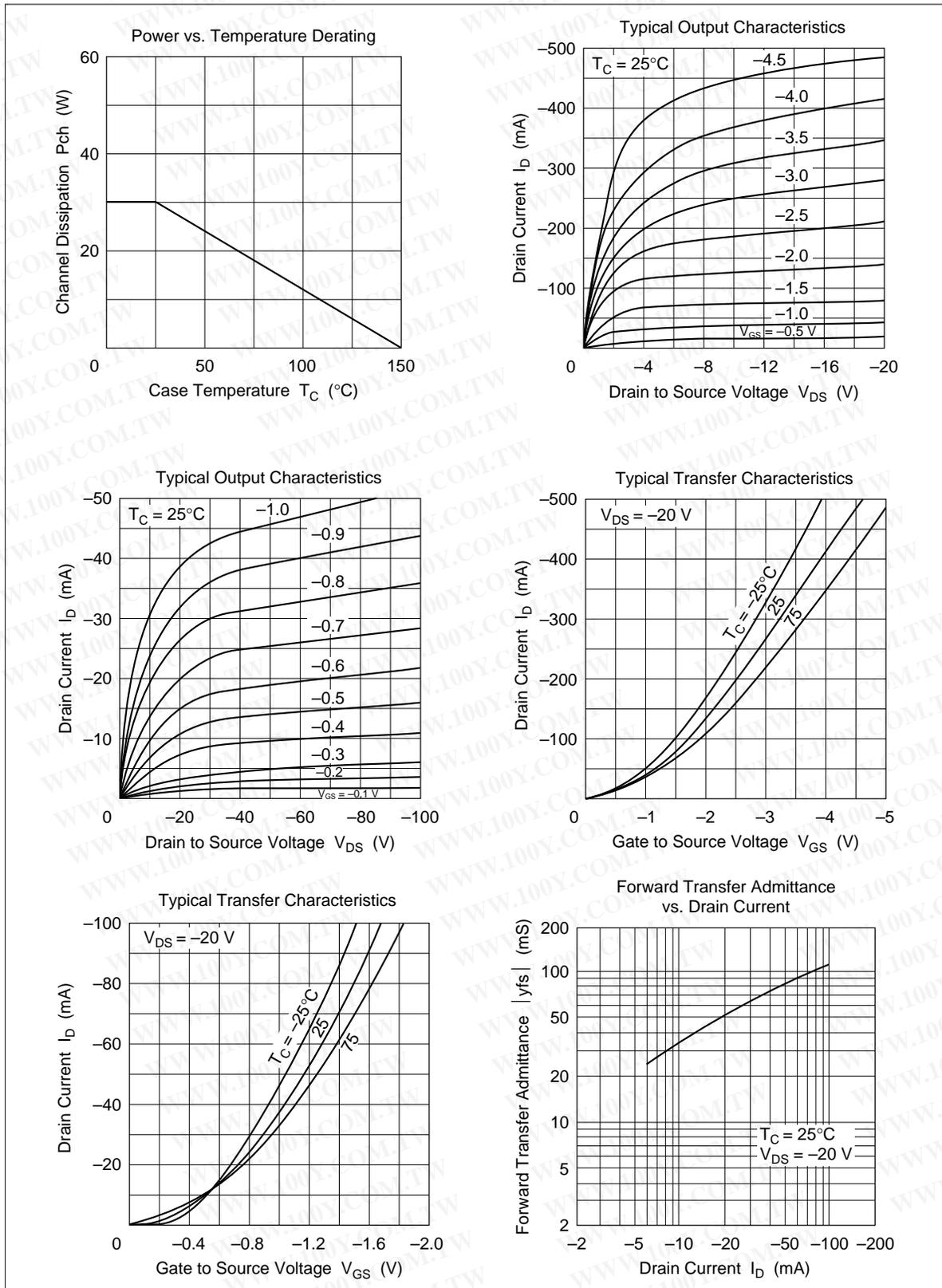
Note 1. Value at $T_C = 25^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

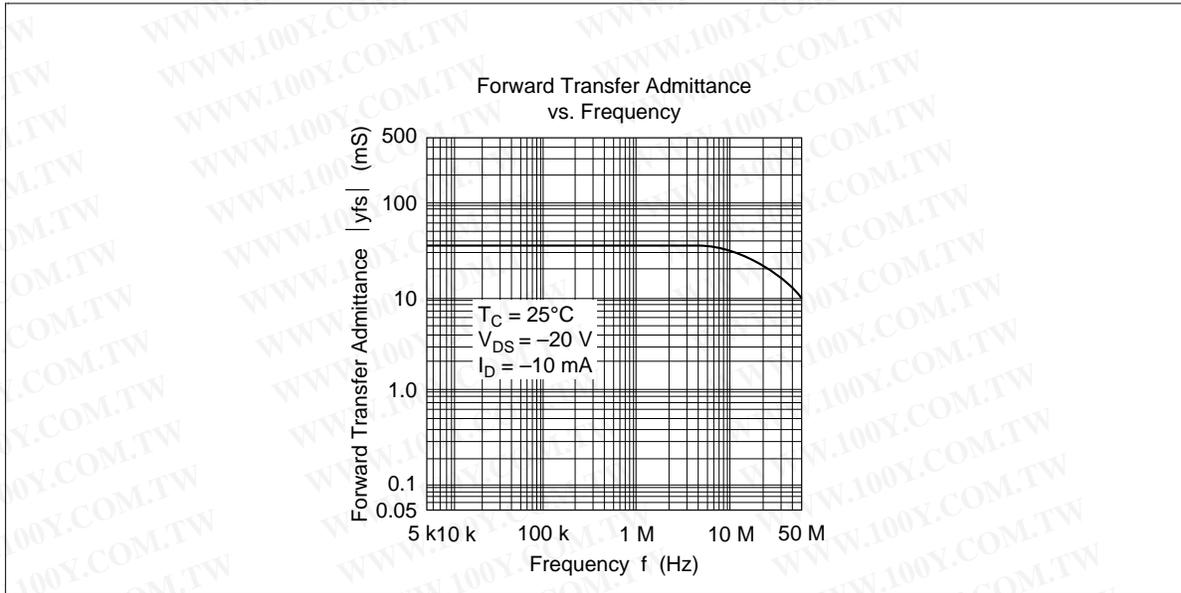
| Item | | Symbol | Min | Typ | Max | Unit | Test conditions |
|------------------------------------|-------|---------------|------|-----|------|------|---|
| Drain to source breakdown voltage | 2SJ76 | $V_{(BR)DSX}$ | -140 | — | — | V | $V_{GS} = 2\text{ V}, I_D = -1\text{ mA}$ |
| | 2SJ77 | | -160 | — | — | V | |
| | 2SJ78 | | -180 | — | — | V | |
| | 2SJ79 | | -200 | — | — | V | |
| Gate to source breakdown voltage | | $V_{(BR)GSS}$ | ±15 | — | — | V | $I_G = \pm 10\ \mu\text{A}, V_{DS} = 0$ |
| Gate to source voltage | | $V_{GS(on)}$ | -0.2 | — | -1.5 | V | $I_D = -10\text{ mA}, V_{DS} = -10\text{ V}^{*1}$ |
| Drain to source saturation voltage | | $V_{DS(sat)}$ | — | — | -2.0 | V | $I_D = -10\text{ mA}, V_{GD} = 0^{*1}$ |
| Forward transfer admittance | | $ y_{fs} $ | 20 | 35 | — | mS | $I_D = -10\text{ mA}, V_{DS} = -20\text{ V}^{*1}$ |
| Input capacitance | | Ciss | — | 120 | — | pF | $V_{DS} = -10\text{ V}, I_D = -10\text{ mA},$ |
| Reverse transfer capacitance | | Crss | — | 4.8 | — | pF | $f = 1\text{ MHz}$ |

Note 1. Pulse test

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